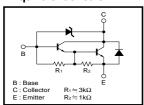
Power transistor (90±10V, 3A)

2SC5060

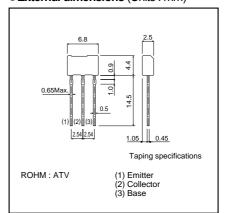
Features

- 1) Built-in zener diode between collector and base.
- 2) Zener diode has low voltage dispersion.
- 3) Strong protection against reverse power surges due to "L" loads.
- 4) Darlington connection for high DC current gain.
- 5) Built-in resistor between base and emitter.
- 6) Built-in damper diode.

●Equivalent circuit



●External dimensions (Units: mm)



● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vcво	90±10	V	
Collector-emitter voltage	Vceo	90±10	V	
Emitter-base voltage	VEBO	6	V	
Collector current	lc	1	A(DC)	
Collector current	Icp	2	A(Pulse)	+1
Collector power dissipation	Pc	1	W	*2
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55~+150	°C	

^{*2} Printed circuit board : 1.7 mm thick, collector copper plating at least 100mm

● Packaging specifications and hfe

Туре	2SC5060
Package	ATV
hre	M
Code	TV2
Basic ordering unit (pieces)	2500

● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	80	-	100	V	Ic=50μA	
Collector-emitter breakdown voltage	BVceo	80	-	100	V	Ic=1mA	
Collector cutoff current	Ісво	-	-	10	μΑ	Vcs=70V	
Emitter cutoff current	Ієво	-	-	3	mA	V _{EB} =5V	
DC current transfer ratio	hre	1000	-	2500	-	VcE=3V, Ic=0.5A *1	
Collector-emitter saturation voltage	VCE(sat)	-	-	1.5	V	Ic/Is=500mA/1mA	
Base-emitter saturation voltage	VBE(sat)	-	-	2	V	Ic/I _B =500mA/1mA *1	
Transition frequency	fτ	-	80	-	MHz	Vcs=5V, Ie=-0.1A, f=30MHz *2	
Output capacitance	Cob	-	20	-	pF	Vce=10V, Ie=0A, f=1MHz	
Turn-on time	ton	-	0.2	-	μs	Ic=0.8A, Rι=50Ω	
Storage time	tstg	-	5	-	μs	I _{B1} =−I _{B2} =8mA Vcc ≒ 40V	
Fall time	tr	-	0.6	-	μs		

^{*1} Measured using pulse current. *2 Transition frequency of the device

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www.datasheetcatalog.com

Datasheets for electronics components.